AMENDMENTS TO THE CLAIMS

1. (Original) A CMOS image sensor comprising:

a semiconductor structure, wherein the semiconductor structure includes a unit pixel area and a pad area;

a metal line formed on the pad area, wherein a portion of the metal line is exposed;

a passivation layer formed on the unit pixel area and on the metal line such that the exposed portion of the metal line is left exposed;

a planarized photoresist formed on a portion of the passivation layer;

a micro-lens formed on a portion of the planarized photoresist; and

an oxide layer formed on the micro-lens, the photoresist and the passivation layer such that the exposed portion is left exposed.

2. (Original) The CMOS image sensor as recited in claim 1, wherein the oxide layer is formed at a temperature of 150°C to 200°C.

3. (Original) The CMOS image sensor as recited in claim 2, wherein the oxide layer is formed to a thickness of 3000 Å to 10000 Å.

4. (Original) The CMOS image sensor as recited in claim 1, wherein the oxide layer is formed to a thickness of 3000 Å to 10000 Å.

5. (Original) The CMOS image sensor as recited in claim 1, wherein the passivation layer includes a nitride layer and a second oxide layer.

6. (Original) The CMOS image sensor as recited in claim 4, further comprising an anti-reflection layer formed on the metal line such that the exposed portion is left exposed.

7. (Original) The CMOS image sensor as recited in claim 1, further comprising an anti-reflection layer formed on the metal line such that the exposed portion is left exposed.

8. (Previously presented) A method for fabricating a CMOS image sensor, comprising:

a) providing a semiconductor structure, wherein the semiconductor structure includes a metal line formed on an upper portion of the semiconductor structure;

b) forming a passivation layer on the metal line;

c) forming a planarized photoresist on a portion of the passivation layer;

d) forming a micro-lens on a portion of the planarized photoresist;

e) forming an oxide layer on the micro-lens, the photoresist and the passivation layer; and

f) forming a pad open mask and etching the oxide layer and the passivation layer to expose a portion of the metal line.

9. (Original) The method as recited in claim 8, wherein the oxide layer is formed at a temperature of 150°C to 200°C.

10. (Original) The method as recited in claim 9, wherein the oxide layer is formed to a thickness of 3000 Å to 10000 Å.

11. (Original) The method as recited in claim 8, wherein the oxide layer is formed to a thickness of 3000 Å to 10000 Å.

12. (Original) The method as recited in claim 8, wherein the passivation layer includes a nitride layer and a second oxide layer.

13. (Original) The method as recited in claim 12, further comprising the step of forming an anti-reflection layer on the metal line.

14. (Original) The method as recited in claim 13, wherein the exposed portion of the metal line is not covered by the anti-reflection layer.

15. (Previously presented) The method as recited in claim 8, further comprising forming an anti-reflection layer on the metal line.

16.-43. (Canceled)